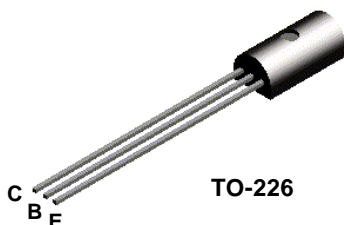


# **TN6719A**



## **NPN High Voltage Amplifier**

This device is designed for use in high voltage applications .  
Sourced from Process 48. See MPSA42 for characteristics.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	300	V
V <sub>CBO</sub>	Collector-Base Voltage	300	V
V <sub>EBO</sub>	Emitter-Base Voltage	7.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		<b>TN6719A</b>	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	1.0 8.0	W mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	125	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	50	°C/W

# NPN High Voltage Amplifier

(continued)

TN6719A

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	300		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$	300		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 1.0 \text{ mA}, I_C = 0$	7.0		V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 200 \text{ V}, I_E = 0$		100	nA
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 6.0 \text{ V}, I_C = 0$		100	nA

### ON CHARACTERISTICS\*

$h_{FE}$	DC Current Gain	$V_{CE} = 10 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 10 \text{ V}, I_C = 30 \text{ mA}$	25 40 40	200	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 30 \text{ mA}, I_B = 3.0 \text{ mA}$		0.75	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 10 \text{ V}, I_C = 30 \text{ mA}$		0.85	V

### SMALL SIGNAL CHARACTERISTICS

$C_{cb}$	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, f = 1.0 \text{ MHz}$		3.5	pF
$h_{fe}$	Small-Signal Current Gain	$I_C = 15 \text{ mA}, V_{CE} = 100 \text{ V},$ $f = 20 \text{ MHz}$	1.5	15	

\*Pulse Test: Pulse Width  $\leq 300 \text{ } \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$